



### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

BV <sub>DSS</sub>	Rds(on)	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	0.99Ω @ V <sub>GS</sub> = 4.5V	0.5A
	1.2Ω @ V <sub>GS</sub> = 2.5V	0.45A
	1.8Ω @ V <sub>GS</sub> = 1.8V	0.37A
	2.4Ω @ V <sub>GS</sub> = 1.5V	0.32A

### **Features**

- Low On-Resistance
- Low Input/Output Leakage
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

## **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Power-management functions
- Backlighting
- Load switches

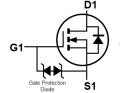
### **Mechanical Data**

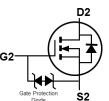
- Package: X2-DFN1010-6
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0015 grams (Approximate)

X2-DFN1010-6 (Type UXC)









D1 G2 S2

D1 D2

S1 G1 D2

**Bottom View** 

**Equivalent Circuit** 

Pin-Out Top View

## Ordering Information (Note 4)

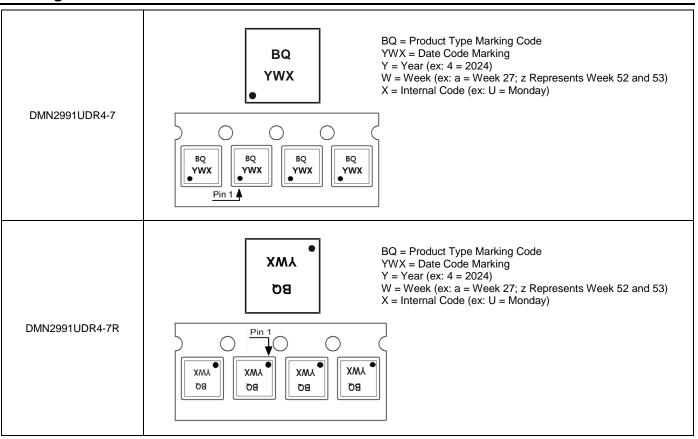
Part Number	Package	Tape Width (mm)	Tape Pitch (mm)	Packing		
Fait Nullibei	Package	rape widin (min)	Tape Fitch (IIIII)	Qty.	Carrier	
DMN2991UDR4-7	X2-DFN1010-6 (Type UXC)	8	4	5000	Tape & Reel	
DMN2991UDR4-7R	X2-DFN1010-6 (Type UXC)	8	4	5000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**



#### Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	2	3	4	5	6	7	8	9	0	1	2	3
Week		1-	-26			27	-52			5	53	
Code		Α	-Z			а	ı-Z				Z	

Internal Cod	e Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	Х	Υ	Z



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	20	V
Gate-Source Voltage	Vgss	±8	V
Continuous Drain Current (Note 5) VGS = 4.5V	ID	0.5 0.4	А
Maximum Continuous Body Diode Forward Currer	Is	0.4	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	Ірм	1.4	Α

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	331	°C/W
Total Power Dissipation (Note 6)		PD	0.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	180	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

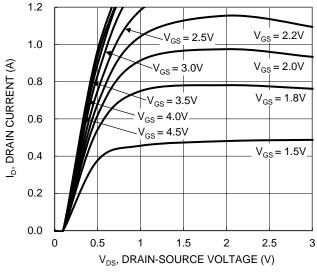
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			, , , , , , , , , , , , , , , , , , ,		I	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	V <sub>G</sub> S = 0V, I <sub>D</sub> = 10µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	-	-	±10	μA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
		_	0.5	0.99		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100mA
Static Drain-Source On-Resistance	Descent	1	0.6	1.2	Ω	$V_{GS} = 2.5V, I_{D} = 50mA$
Static Dialif-Source Off-Resistance	RDS(ON)	1	0.7	1.8	12	$V_{GS} = 1.8V$ , $I_D = 20mA$
		-	0.9	2.4		$V_{GS} = 1.5V, I_D = 10mA$
Diode Forward Voltage	VsD	-	0.8	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	_	14.6	_		
Output Capacitance	Coss	_	4.7	_	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	3.2	_		1 – 1.00112
Total Gate Charge	$Q_g$	1	0.28	_		45)/ 45)/
Gate-Source Charge	Qgs	_	0.04	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V$ $I_{D} = 250 \text{mA}$
Gate-Drain Charge	$Q_{gd}$	_	0.1	_		ID = 230IIIA
Turn-On Delay Time	td(ON)	_	7.1			
Turn-On Rise Time	t <sub>R</sub>	-	18	_	ne	$V_{DD} = 10V, V_{GS} = 4.5V$ $R_L = 47\Omega, R_G = 10\Omega$
Turn-Off Delay Time	t <sub>D(OFF)</sub>		125	_	ns	$R_L = 47\Omega$ , $R_G = 10\Omega$ $I_D = 200 \text{mA}$
Turn-Off Fall Time	tF	_	56.9	_		15 - 2001171

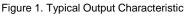
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
   Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
   Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to production testing.







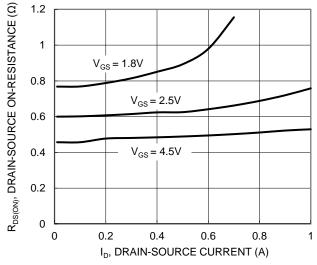


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

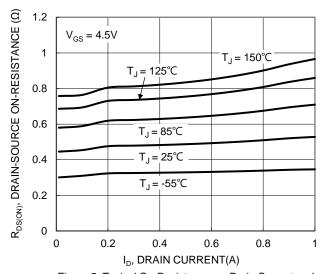


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

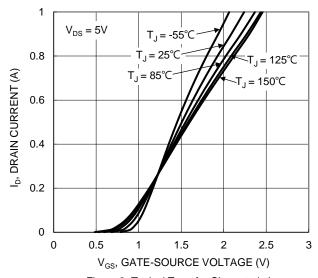


Figure 2. Typical Transfer Characteristic

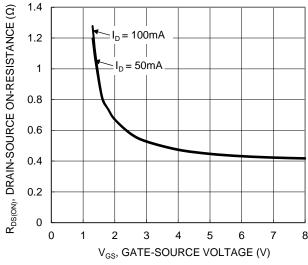


Figure 4. Typical Transfer Characteristic

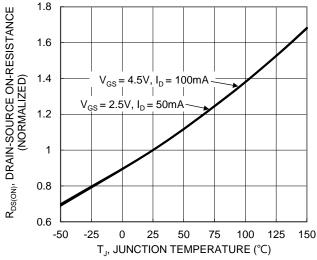


Figure 6. On-Resistance Variation with Junction Temperature



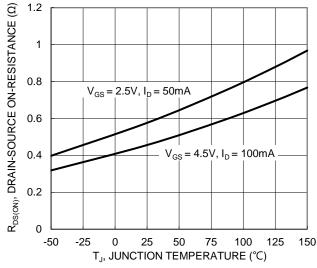


Figure 7. On-Resistance Variation with Junction Temperature

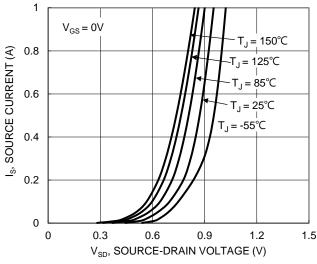
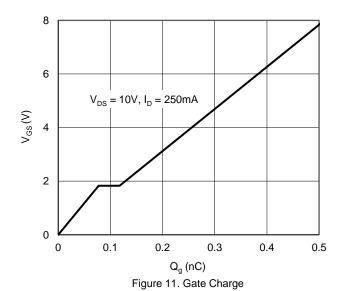


Figure 9. Diode Forward Voltage vs. Current



 $V_{GS(TH)}$ , GATE THRESHOLD VOLTAGE (V) 0.9 0.8  $I_D = 1mA$ 0.7 0.6  $I_D = 250 \mu A$ 0.5 0.4 0.3 0.2 0.1 0 50 75 100 125 -50 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature

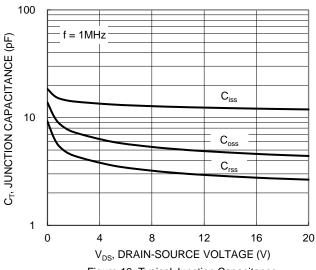


Figure 10. Typical Junction Capacitance

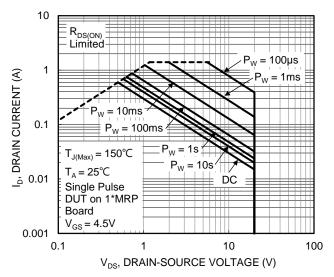


Figure 12. SOA, Safe Operation Area



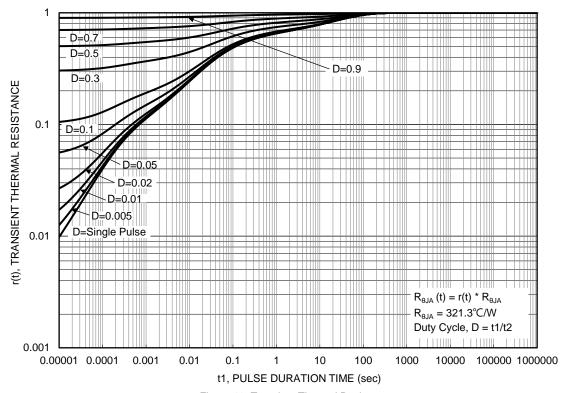


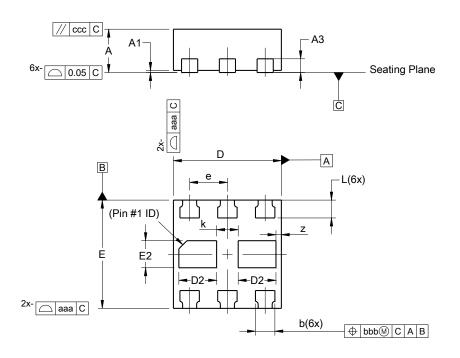
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## X2-DFN1010-6 (Type UXC)

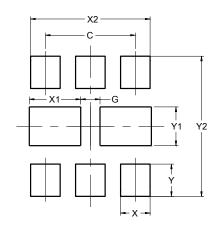


X2-DFN1010-6									
(Type UXC)									
Dim	Min	Max	Тур						
Α		0.40	0.39						
A1	-	0.05							
A3			0.127						
b	0.13	0.23	0.18						
D	0.95	1.05	1.00						
D2	0.30	0.40	0.35						
Е	0.95	1.05	1.00						
E2	0.20	0.30	0.25						
е	0.	350 BS	С						
L	0.115	0.215	0.165						
k			0.20						
Z	0.02	0.08	0.05						
aaa	0.08								
bbb	0.07								
CCC	0.05								
All	Dimensi	ions in							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## X2-DFN1010-6 (Type UXC)



Dimensions	Value			
	(in mm)			
С	0.700			
G	0.300			
X	0.230			
X1	0.450			
X2	0.930			
Υ	0.250			
Y1	0.300			
Y2	1.085			



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